

ABSTRACT OF THE DISCLOSURE

A process for manufacturing a phase change memory cell, comprising the steps of: forming a resistive element; forming a delimiting structure having an aperture over the resistive element; forming a memory portion of a phase change material in the aperture, the resistive element and the memory portion being in direct electrical contact and defining a contact area of sublithographic extension. The step of forming a memory portion further includes filling the aperture with the phase change material and removing from the delimiting structure an exceeding portion of the phase change material exceeding the aperture.

854163.414 / 472658_1.DOC